

April 2011

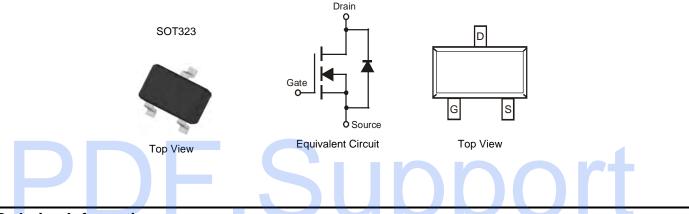
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- High Drain-Source Voltage Rating
- Lead Free/RoHS Compliant (Note 1)
- "Green" Device (Notes 2 & 3)
- Qualified to AEC-Q101 Standards for High Reliability

Mechanical Data

- Case: SOT323
- Case Material: Molded Plastic, "Green" Molding Compound, Note 3. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Matte Tin Finish annealed over Alloy 42 Leadframe (Lead Free Plating). Solderable per MIL-STD-202, Method 208
- Weight: 0.006 grams (approximate)



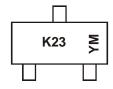
Ordering Information (Notes 3 & 4)

Part Number	Case	Packaging		
BSS123W-7-F	SOT323	3000/Tape & Reel		

Notes:

- 1. No purposefully added lead.
- 2. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com.
- 3. Product manufactured with Date Code 0627 (week 27, 2006) and newer are built with Green Molding Compound. Product manufactured prior to Date Code 0627 are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.
- 4. For packaging details, go to our website at http://www.diodes.com.

Marking Information



K23 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: N = 2002)M = Month (ex: 9 = September)

Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012	2013	2014	2015	2016	2017
Code	N	Р	R	S	Т	U	V	W	Х	Υ	Z	Α	В	С	D	Е
Month	Jan	F	eb	Mar	Apr	M	lay	Jun	Jul	Α	ug	Sep	Oct	N	ov	Dec
Code	1		2	3	4		5	6	7		3	9	0	1	1	D



Maximum Ratings @T_A = 25°C unless otherwise specified

Characteri	istic	Symbol	Value	Units
Drain-Source Voltage		V _{DSS}	100	V
Drain-Gate Voltage $R_{GS} \le 20$ KΩ		V_{DGR}	100	V
Gate-Source Voltage	Continuous	V_{GSS}	±20	V
Drain Current (Note 5)	Continuous Pulsed	I _D I _{DM}	170 680	mA

Thermal Characteristics @TA = 25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	P_{D}	200	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{ hetaJA}$	625	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

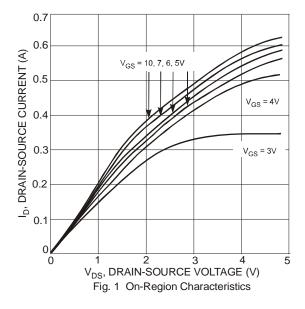
Electrical Characteristics @T_A = 25°C unless otherwise specified

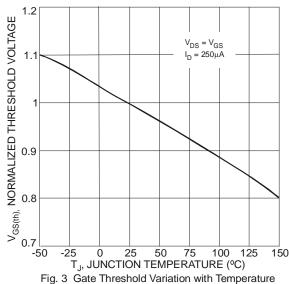
	_					
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	100		_	V	$V_{GS} = 0V, I_D = 250\mu A$
Zero Gate Voltage Drain Current	I _{DSS}		_	1.0	μΑ	$V_{DS} = 100V, V_{GS} = 0V$
Zero Gate Voltage Brain Gurierit				10	nA	$V_{DS} = 20V$, $V_{GS} = 0V$
Gate-Body Leakage, Forward	I _{GSSF}		_	50	nA	$V_{GS} = 20V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	$V_{GS(th)}$	0.8	1.4	2.0	V	$V_{DS} = V_{GS}$, $I_D = 1mA$
Static Drain-Source On-Resistance	R _{DS} (ON)	_	_	6.0	Ω	$V_{GS} = 10V, I_D = 0.17A$
Static Dialif-Source Off-Resistance		—	_	10	5.2	$V_{GS} = 4.5V, I_D = 0.17A$
Forward Transconductance	g _{FS}	80	370	_	mS	$V_{DS} = 10V$, $I_D = 0.17A$, $f = 1.0KHz$
Drain-Source Diode Forward Voltage	V_{SD}	_	0.84	1.3	V	$V_{GS} = 0V, I_{S} = 0.34A$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}		29	60	рF	
Output Capacitance	Coss		10	15	рF	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$
Reverse Transfer Capacitance	C _{rss}		2	6	рF	
SWITCHING CHARACTERISTICS						
Turn-On Rise Time	t _r	_	_	8	ns	
Turn-Off Fall Time	t _f	_	_	16	ns	$V_{DD} = 30V, I_D = 0.28A,$
Turn-On Delay Time	t _{D(ON)}			8	ns	$R_{GEN} = 50\Omega$, $V_{GS} = 10V$
Turn-Off Delay Time	t _{D(OFF)}	_	_	13	ns	

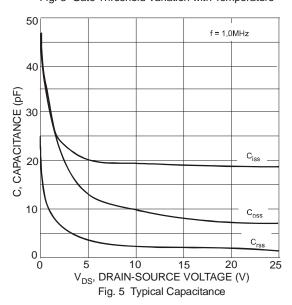
Notes:

^{5.} Part mounted on FR-4 board with recommended pad layout, which can be found on our website at http://www.diodes.com. 6. Short duration pulse test used to minimize self-heating effect.









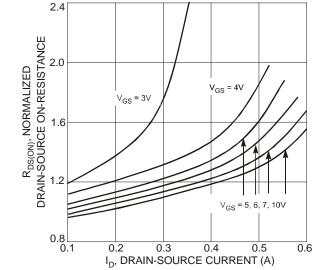


Fig. 2 On-Resistance Variation with Gate Voltage and Drain-Source Current

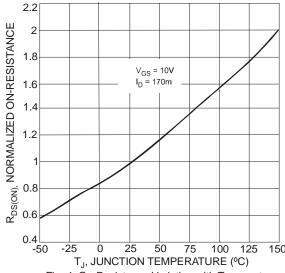
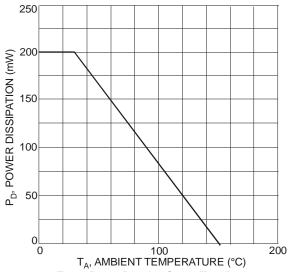
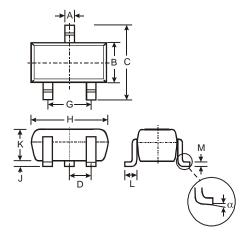


Fig. 4 On-Resistance Variation with Temperature



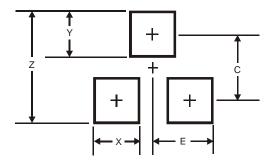


Package Outline Dimensions



SOT323								
Dim	Min	Max	Тур					
Α	0.25	0.40	0.30					
В	1.15	1.35	1.30					
С	2.00	2.20	2.10					
D	-	-	0.65					
G	1.20	1.40	1.30					
Н	1.80	2.20	2.15					
J	0.0	0.10	0.05					
K	0.90	1.00	1.00					
L	0.25	0.40	0.30					
М	0.10	0.18	0.11					
α	0°	8°	-					
All Dimensions in mm								

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.8
Х	0.7
Y	0.9
С	1.9
Е	1.0



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